

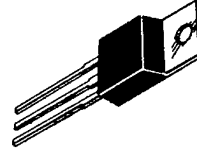
MOTOROLA SEMICONDUCTOR TECHNICAL DATA

NPN BDW39 thru BDW43 **PNP BDW44 thru BDW48**

DARLINGTON COMPLEMENTARY SILICON POWER TRANSISTORS

- ... designed for general purpose and low speed switching applications.
- High DC Current Gain - $h_{FE} = 2500$ (typ.) @ $I_C = 5.0$ Adc.
- Collector Emitter Sustaining Voltage @ 30 mAdc:
 $V_{CE(sus)} = 45$ Vdc (min.) - BDW39/BDW44
 60 Vdc (min.) - BDW40/BDW45
 80 Vdc (min.) - BDW41/BDW46
 100 Vdc (min.) - BDW42/BDW47
 120 Vdc (min.) - BDW43/BDW48
- Low Collector Emitter Saturation Voltage:
 $V_{CE(sat)} = 2.0$ Vdc (max.) @ $I_C = 5.0$ Adc
 3.0 Vdc (max.) @ $I_C = 10.0$ Adc
- Monolithic Construction with Built-In Base Emitter Shunt resistors
- TO-220AB Compact Package
- TO-66 Lead form also available ordered with ".66" suffix.

DARLINGTON 15 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 45-60-80-100-120 VOLTS 85 WATTS



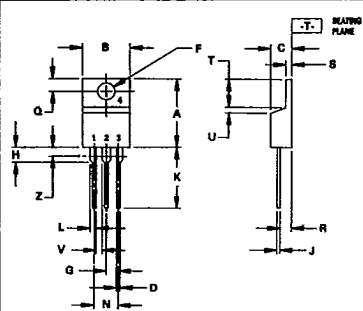
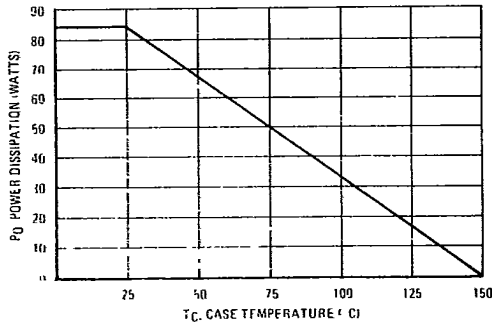
MAXIMUM RATINGS

Rating	Symbol	BDW39 BDW44	BDW40 BDW45	BDW41 BDW46	BDW42 BDW47	BDW43 BDW48	Unit
Collector-Emitter Voltage	V_{CE}	45	60	80	100	120	Vdc
Collector-Base Voltage	V_{CB}	45	60	80	100	120	Vdc
Emitter-Base Voltage	V_{EB}	5.0					Vdc
Collector Current - Continuous	I_C	15					Adc
Base Current	I_B	0.5					Adc
Total Device Dissipation Tc = 25 C Derate above 25 C	P_D	85 0.68					Watts W/C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to -150					C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max.	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.47	C/W

FIGURE 1 - POWER TEMPERATURE DERATING CURVE



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION INCH.
 3. DIM Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	14.48	15.75	0.570	0.620
B	9.65	10.28	0.380	0.405
C	4.07	4.82	0.160	0.190
D	0.64	0.98	0.025	0.039
F	3.41	3.73	0.142	0.147
G	2.42	2.66	0.095	0.106
H	2.80	3.93	0.110	0.155
J	0.48	0.71	0.018	0.028
K	12.70	14.27	0.500	0.562
L	1.15	1.39	0.045	0.055
N	4.83	5.33	0.190	0.210
Q	2.54	3.04	0.100	0.120
R	2.54	2.79	0.100	0.110
S	1.15	1.39	0.045	0.055
T	5.97	6.47	0.235	0.255
U	0.00	1.27	0.000	0.050
V	1.15	—	0.045	—
Z	—	2.54	—	0.090

- STYLE 1
 PIN 1 BASE
 2. COLLECTOR
 3. EMITTER
 4. COLLECTOR

CASE 221A-04 TO-220AB

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BDW39, BDW40, BDW41, BDW42, BDW43 NPN
 BDW44, BDW45, BDW46, BDW47, BDW48 PNP

T-33-31

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ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector Emitter Sustaining Voltage (1) ($I_C = 30 \text{ mAdc}, I_B = 0$)	BDW39/BDW44 BDW40/BDW45 BDW41/BDW46 BDW42/BDW47 BDW43/BDW48	$V_{CE(sus)}$	45 60 80 100 120	— — — — —	Vdc
Collector Cutoff Current ($V_{CE} = 22.5 \text{ Vdc}, I_B = 0$) ($V_{CE} = 30 \text{ Vdc}, I_B = 0$) ($V_{CE} = 40 \text{ Vdc}, I_B = 0$) ($V_{CE} = 50 \text{ Vdc}, I_B = 0$) ($V_{CE} = 60 \text{ Vdc}, I_B = 0$)	BDW39/BDW44 BDW40/BDW45 BDW41/BDW46 BDW42/BDW47 BDW43/BDW48	I_{CEO}	— — — — —	2.0 2.0 2.0 2.0 2.0	mAdc
Collector Cutoff Current ($V_{CB} = 45 \text{ Vdc}, I_E = 0$) ($V_{CB} = 60 \text{ Vdc}, I_E = 0$) ($V_{CB} = 80 \text{ Vdc}, I_E = 0$) ($V_{CB} = 100 \text{ Vdc}, I_E = 0$) ($V_{CB} = 120 \text{ Vdc}, I_E = 0$)	BDW39/BDW44 BDW40/BDW45 BDW41/BDW46 BDW42/BDW47 BDW43/BDW48	I_{CBO}	— — — — —	1.0 1.0 1.0 1.0 1.0	mAdc
Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}, I_C = 0$)		I_{EBO}	—	2.0	mAdc
ON CHARACTERISTICS (1)					
DC Current Gain ($I_C = 5.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$) ($I_C = 10 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$)		h_{FE}	1000 250	— —	
Collector-Emitter Saturation Voltage ($I_C = 5.0 \text{ Adc}, I_B = 10 \text{ mAdc}$) ($I_C = 10 \text{ Adc}, I_B = 50 \text{ mAdc}$)		$V_{CE(sat)}$	— —	2.0 3.0	Vdc
Base-Emitter On Voltage ($I_C = 10 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$)		$V_{BE(on)}$	—	3.0	Vdc
SECOND BREAKDOWN (2)					
Second Breakdown Collector Current with Base Forward Biased BDW39/BDW40/BDW41/BDW42/BDW43 BDW44/BDW45/BDW46/BDW47/BDW48	$V_{CE} = 28.4 \text{ Vdc}$ $V_{CE} = 40 \text{ Vdc}$ $V_{CE} = 22.5 \text{ Vdc}$ $V_{CE} = 36 \text{ Vdc}$	$I_{S/b}$	3.0 1.2 3.8 1.2	— — — —	Adc
DYNAMIC CHARACTERISTICS					
Magnitude of common emitter small signal short circuit current transfer ratio ($I_C = 3.0 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}, f = 1.0 \text{ MHz}$)		f_T	4.0	—	MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 0.1 \text{ MHz}$) BDW39/BDW40/BDW41/BDW42/BDW43 BDW44/BDW45/BDW46/BDW47/BDW48		C_{ob}	— —	200 300	pF
Small-Signal Current Gain ($I_C = 3.0 \text{ Adc}, V_{CE} = 3.0 \text{ Vdc}, f = 1.0 \text{ kHz}$)		h_{fe}	300	—	

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Indicates JEDEC Registered Data.

(1) Pulse Test: Pulse Width = 300 μs , Duty Cycle = 2.0%.

(2) Pulse Test non repetitive: Pulse Width = 250 ms.

BDW39, BDW40, BDW41, BDW42, BDW43 NPN
BDW44, BDW45, BDW46, BDW47, BDW48 PNP

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FIGURE 2 - SWITCHING TIMES TEST CIRCUIT

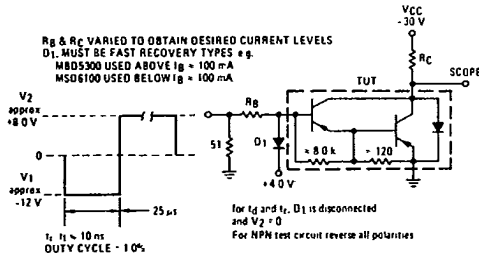


FIGURE 3 - SWITCHING TIMES

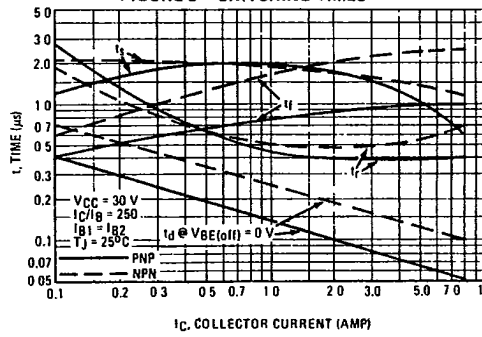
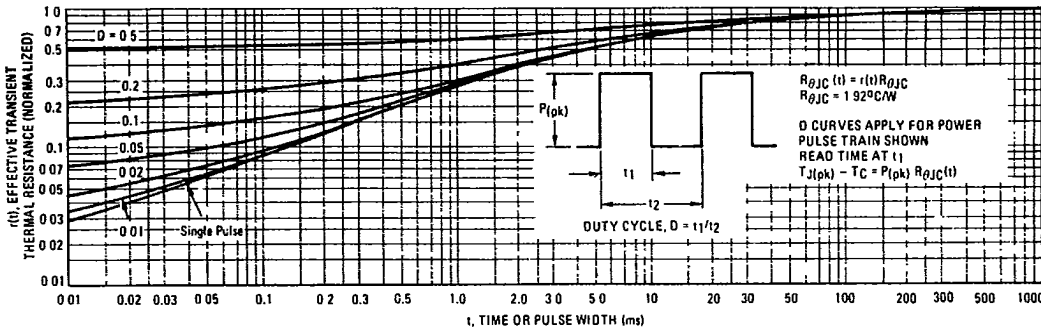


FIGURE 4 - THERMAL RESPONSE



ACTIVE-REGION SAFE OPERATING AREA

FIGURE 5 - BDW39 THRU BDW43

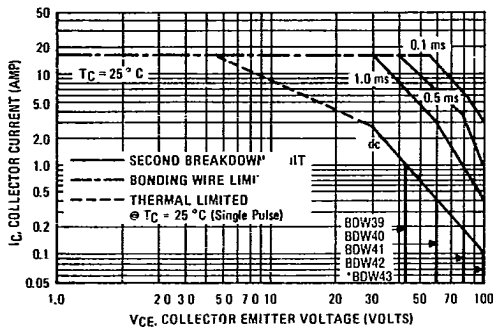
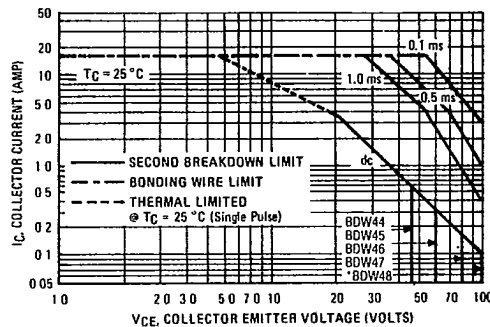


FIGURE 6 - BDW44 THRU BDW48



There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Fig. 5 and 6 is based on $T_{J(pk)} =$

200°C ; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 200^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Fig. 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown. (See an-415).

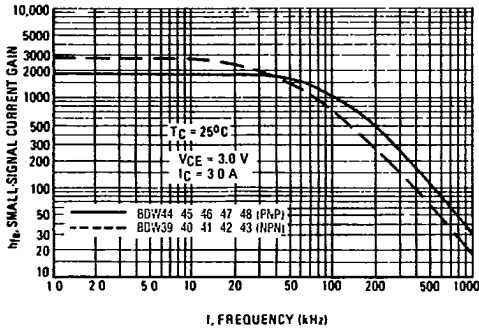
*Linear extrapolation

BDW39, BDW40, BDW41, BDW42, BDW43 NPN
 BDW44, BDW45, BDW46, BDW47, BDW48 PNP

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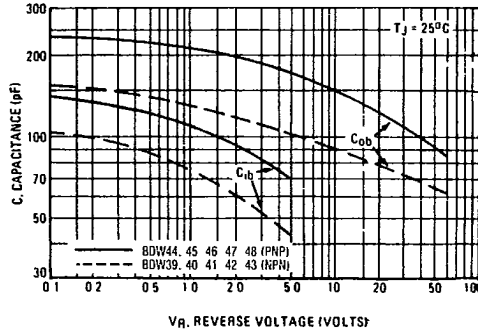
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FIGURE 7 - SMALL-SIGNAL CURRENT GAIN



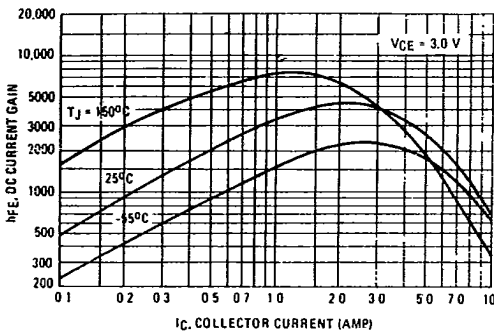
BDW39, 40, 41, 42, 43 (NPN)

FIGURE 8 - CAPACITANCE

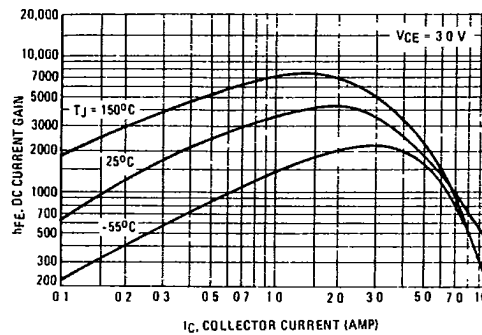


BDW44, 45, 46, 47, 48 (PNP)

FIGURE 9 - DC CURRENT GAIN



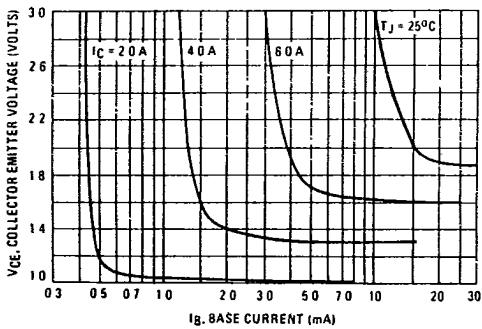
BDW39, 40, 41, 42, 43 (NPN)



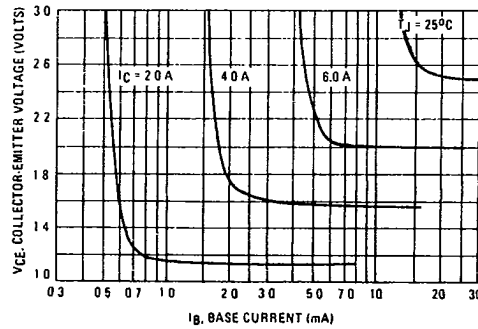
BDW44, 45, 46, 47, 48 (PNP)

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FIGURE 10 - COLLECTOR SATURATION REGION



BDW39, 40, 41, 42, 43 (NPN)



BDW44, 45, 46, 47, 48 (PNP)

BDW39, 40, 41, 42, 43 (NPN)

BDW44, 45, 46, 47, 48 (PNP)

FIGURE 11 - "ON" VOLTAGES

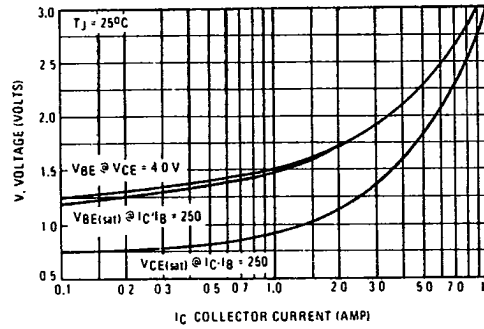
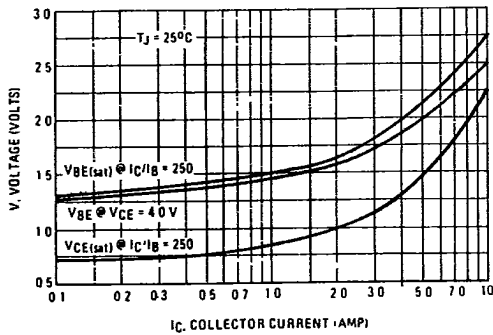


FIGURE 12 - TEMPERATURE COEFFICIENTS

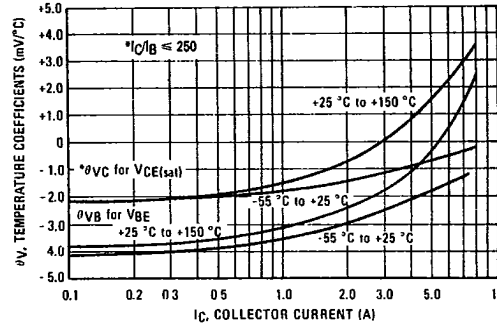
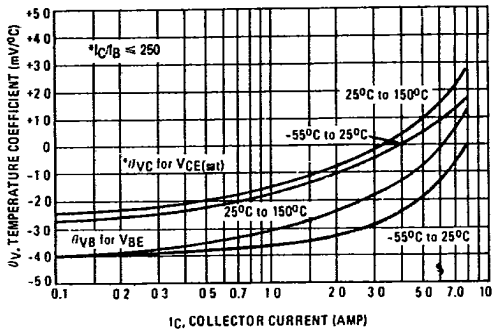
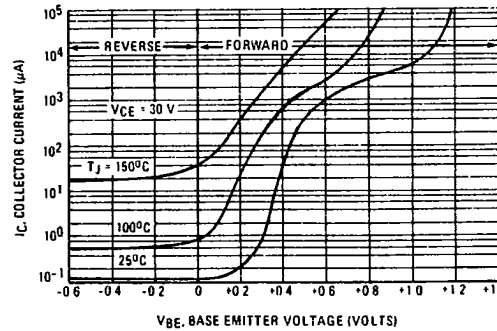
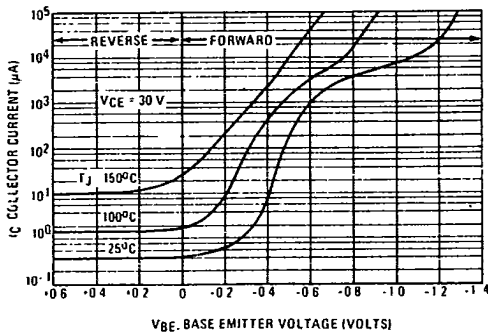


FIGURE 13 - COLLECTOR CUT-OFF REGION



BDW39, BDW40, BDW41, BDW42, BDW43 NPN
BDW44, BDW45, BDW46, BDW47, BDW48 PNP

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FIGURE 14 - DARLINGTON SCHEMATIC

